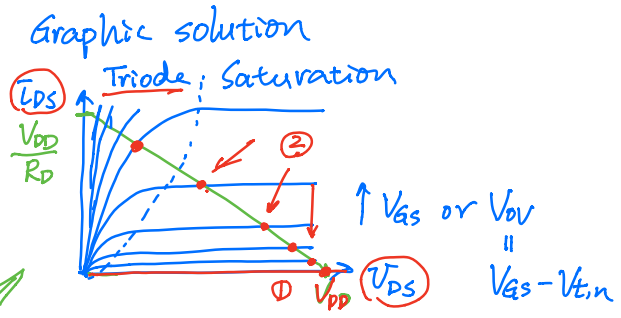
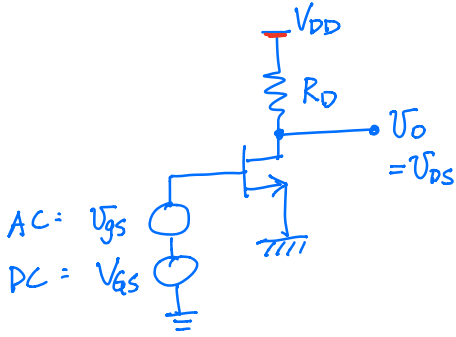
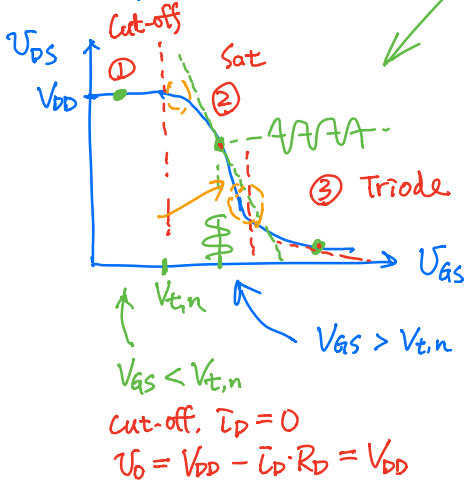


Small-signal model

* No OH today
* Thu OH v or Email



Transfer characteristics (Output -vs- input)



Load Line \rightarrow KVL

$$V_{DD} = \bar{I}_D R_D + \bar{V}_{DS}$$

EE16 A/B : Digital operation
Inverter : ① cut-off \rightarrow "1"
 ③ Triode \rightarrow "0"

EE105 : Analog operation
Amplifier : ② Saturation

$V_{GS} > V_{tn}$, $V_O = V_{DD} - \bar{I}_D R_D$, NMOS in saturation

$$= V_{DD} - \frac{1}{2} k_n V_{OV}^2 \cdot R_D$$

$$= V_{DD} - \frac{1}{2} k_n (V_{GS} - V_{tn})^2 \cdot R_D$$

Amplifier

ac output \rightarrow $V_{GS} + V_{DS} = V_{DD} - \frac{1}{2} k_n (V_{GS} + \bar{V}_{GS} - V_{tn})^2 \cdot R_D$

\swarrow ac input

solve DC first : $V_{DS} = V_{DD} - \frac{1}{2} k_n (V_{GS} - V_{tn})^2 \cdot R_D$

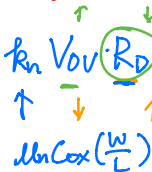
Voltage gain

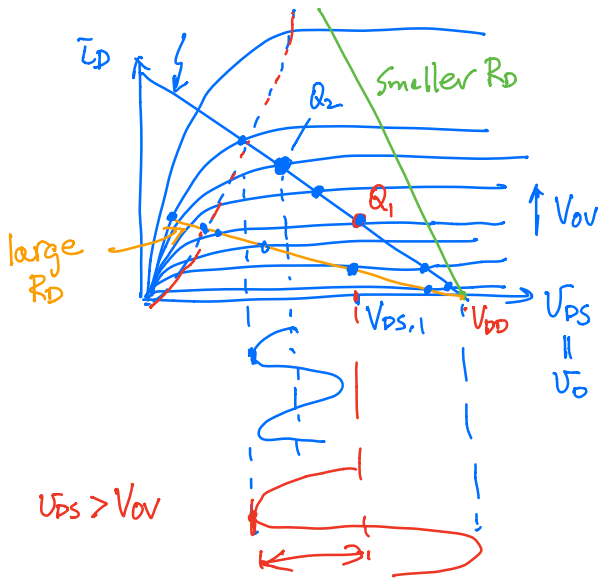
$$A_v = \left. \frac{\partial V_{DS}}{\partial V_{GS}} \right|_Q = -k_n (V_{GS} - V_{tn}) R_D = -k_n V_{OV} R_D \Leftarrow$$

slope = $\frac{1}{R_D}$

\uparrow Bias point
 $V_{GS} = V_{GS}$ (i.e., $V_{GS} = 0$)

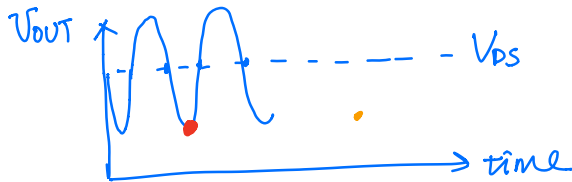
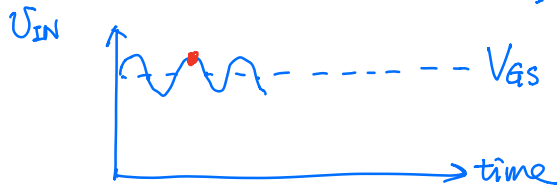
Negative





$V_{DS} > V_{OV}$

maximum swing $V_{OV} \leq V_{DS} \leq V_{DD}$

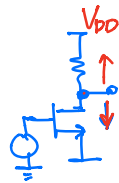


For large A_v

- * Bias at high $V_{GS} \rightarrow V_{OV}$
e.g. bias at Q_2
 \rightarrow Sacrifice output voltage swing
- * Q_1 is better Q_2 for swing
- * Increase R_D
 \rightarrow Use lower V_{GS} , or V_{OV}

To stay in small-signal input signal constraint

Need $V_{DS} \geq V_{OV} = V_{GS} - V_{th}$



$$V_{DS, \min} = V_{DS} - \underline{V_{ds}} \geq \underline{V_{GS, \max}} - \underline{V_{th}}$$

$$V_{DS} - \underline{V_{ds}} \geq \underline{V_{GS}} + \underline{V_{gs}}$$

$$V_{ds} = |A_v| \cdot \underline{v_{gs}}$$

$$\underline{V_{GS}} \leq \frac{V_{DS} - V_{OV}}{1 + |A_v|}$$

$$A_v = -g_m V_{OV} R_D$$

180° Phase shift

$$|A_v| > 1$$

output amplitude larger than input.

"Easy Way" \rightarrow small-signal model

$$\bar{I}_D(V_{GS}, V_{DS}) = \frac{1}{2} k_n (V_{GS} - V_{th})^2 \underbrace{(1 + \lambda V_{DS})}_{\substack{\uparrow \\ \text{consider channel length} \\ \text{modulations}}}$$

To simplify, $\lambda = 0$

$$\bar{I}_D = \frac{1}{2} k_n (V_{GS} - V_{th})^2$$

$$\bar{I}_D = I_D + \underbrace{\frac{\partial \bar{I}_D}{\partial V_{GS}} \bigg|_Q}_{\text{small-signal gain}} \cdot \underline{v_{gs}}$$

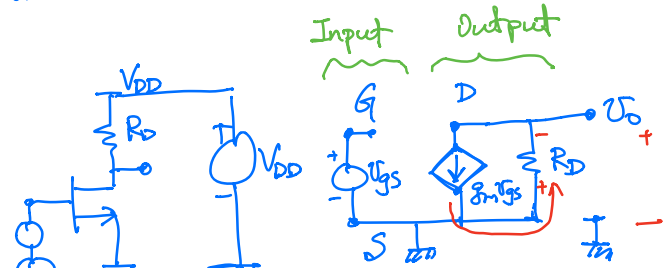
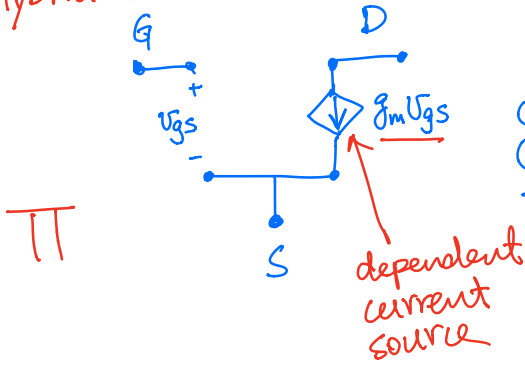
$$\bar{I}_D = I_D + \bar{I}_d$$

$$V_{GS} = V_{GS} + \underline{v_{gs}}$$

$$I_D = I_{D0} + g_m \cdot v_{gs}$$

$$g_m = k_n (V_{GS} - V_{t,n}) = k_n V_{ov}$$

Equivalent circuit:
Hybrid π model



DC voltage source \rightarrow Short circuit
DC current source \rightarrow Open

$$v_o = - (g_m v_{gs}) \cdot R_D$$

↑
current

Circuit
① Solve bias point, Q
 V_{GS}, I_D, V_{GS}

② Find small-signal parameters

$$g_m = k_n V_{ov} = k_n (V_{GS} - V_{t,n}) \leftarrow \text{only dep on DC values i.e. Q point}$$

③ Replace $\frac{1}{s}$ with \rightarrow

Replace DC voltage source with short ckt

Replace DC current " " open ckt

④ KCL, KVL for AC equivalent circuit

Complete model

$$I_D = \frac{1}{2} k_n (V_{GS} + v_{gs} - V_{t,n})^2 (1 + \lambda (V_{DS} + v_{ds}))$$

$$I_D = I_{D0} + \left. \frac{\partial I_D}{\partial V_{GS}} \right|_Q v_{gs} + \left. \frac{\partial I_D}{\partial V_{DS}} \right|_Q v_{ds}$$

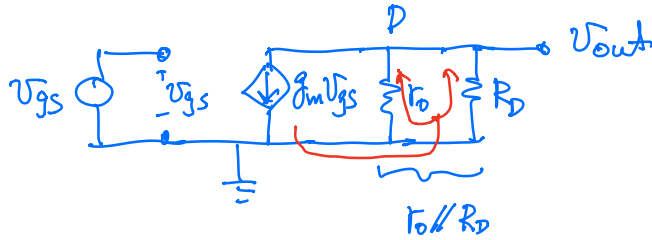
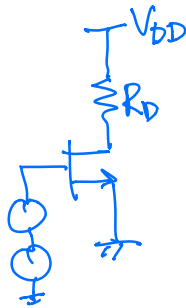
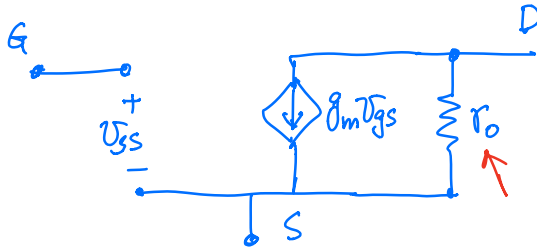
$$= I_{D0} + g_m v_{gs} + \frac{v_{ds}}{r_o} \leftarrow$$

$$r_o = \frac{1}{\lambda I_D}$$

$$\frac{\partial I_D}{\partial V_{DS}} = \lambda \cdot \underbrace{\frac{1}{2} \mu_n C_{ox} (V_{GS} - V_{th,n})^2}_{I_D} = \lambda I_D = \frac{1}{r_o}$$

$$- \frac{\Delta V_{DS}}{\Delta I_{DS}} = r_o$$

Hybrid π model



$$A_v = -g_m (r_o // R_D)$$

impact of output resistance of the MOS on overall gain